

### **IGBT** Module

#### SK45GH063

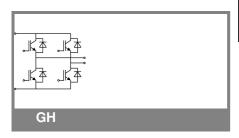
Preliminary Data

#### **Features**

- Compact design
- · One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- N channel, homogeneous Silicon structure (NPT-Non punchtrough IGBT)
- High short circuit capability
- Low tail current with low temperature dependence
- UL recognized, file no. E63532

### Typical Applications\*

- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS



<b>Absolute Maximum Ratings</b> T <sub>s</sub> = 25 °C, unless otherwise specified						
Symbol	Conditions		Values	Units		
IGBT						
$V_{CES}$	T <sub>j</sub> = 25 °C		600	V		
I <sub>C</sub>	T <sub>j</sub> = 125 °C	T <sub>s</sub> = 25 °C	45	Α		
		$T_s = 80  ^{\circ}C$	30	Α		
I <sub>CRM</sub>	I <sub>CRM</sub> = 2 x I <sub>Cnom</sub>		100	Α		
$V_{\rm GES}$			± 20	٧		
t <sub>psc</sub>	$V_{CC}$ = 300 V; $V_{GE} \le$ 20 V; $V_{CES}$ < 600 V	T <sub>j</sub> = 125 °C	10	μs		
Inverse D	iode			•		
$I_{F}$	T <sub>j</sub> = 150 °C	$T_s = 25 ^{\circ}C$	57	Α		
		$T_s = 80  ^{\circ}C$	38	Α		
I <sub>FRM</sub>	I <sub>FRM</sub> = 2 x I <sub>Fnom</sub>		100	Α		
I <sub>FSM</sub>	$t_p$ = 10 ms; half sine wave	T <sub>j</sub> = 150 °C	440	Α		
Module						
$I_{t(RMS)}$				Α		
T <sub>vj</sub>			-40 <b>+</b> 150	°C		
T <sub>stg</sub>			-40 +125	°C		
V <sub>isol</sub>	AC, 1 min.		2500	V		

<b>Characteristics</b> T <sub>s</sub> = 25 °C, unless otherwise specified							
Symbol	Conditions		min.	typ.	max.	Units	
IGBT						•	
$V_{GE(th)}$	$V_{GE} = V_{CE}$ , $I_C = 1 \text{ mA}$		4,5	5,5	6,5	V	
I <sub>CES</sub>	V <sub>GE</sub> = 0 V, V <sub>CE</sub> = V <sub>CES</sub>	T <sub>j</sub> = 25 °C			0,15	mA	
		T <sub>j</sub> = 125 °C				mA	
I <sub>GES</sub>	V <sub>CE</sub> = 0 V, V <sub>GE</sub> = 30 V	T <sub>j</sub> = 25 °C			120	nA	
		T <sub>j</sub> = 125 °C				nA	
$V_{CE0}$		T <sub>j</sub> = 25 °C		1		V	
		T <sub>j</sub> = 125 °C		1,1		V	
r <sub>CE</sub>	V <sub>GE</sub> = 15 V	T <sub>j</sub> = 25°C		20		mΩ	
		T <sub>j</sub> = 125°C				mΩ	
V <sub>CE(sat)</sub>	I <sub>Cnom</sub> = 50 A, V <sub>GE</sub> = 15 V	T <sub>j</sub> = 25°C <sub>chiplev.</sub>		2,1	2,5	V	
		$T_j = 125^{\circ}C_{chiplev}$				V	
C <sub>ies</sub>				2,2		nF	
C <sub>oes</sub>	$V_{CE} = 25, V_{GE} = 0 V$	f = 1 MHz				nF	
C <sub>res</sub>				0,2		nF	
$Q_G$	V <sub>GE</sub> = 0 20 V			155		nC	
t <sub>d(on)</sub>				45		ns	
t <sub>r</sub>	$R_{Gon} = 22 \Omega$	V <sub>CC</sub> = 300V		35		ns	
E <sub>on</sub>	D 00.0	I <sub>C</sub> = 30A		1,4		mJ	
<sup>L</sup> d(off)	$R_{Goff} = 22 \Omega$	T <sub>j</sub> = 125 °C V <sub>GE</sub> =±15V		250 25		ns ns	
t <sub>f</sub> E <sub>off</sub>		VGE-113V		1,2		mJ	
R <sub>th(j-s)</sub>	per IGBT				1	K/W	



SEMITOP® 3

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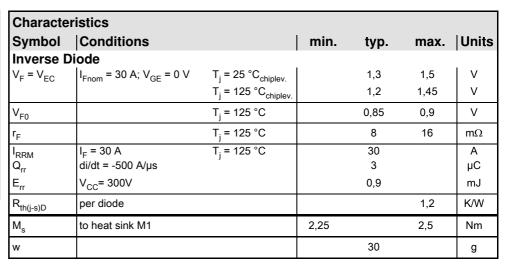
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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

